

# SN74CBTLV16212 LOW-VOLTAGE 24-BIT FET BUS-EXCHANGE SWITCH

SCDS044E – DECEMBER 1997 – REVISED AUGUST 1999

- **4- $\Omega$  Switch Connection Between Two Ports**
- **Isolation Under Power-Off Conditions**
- **Break-Before-Make Feature**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **Package Options Include Plastic Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV), and 300-mil Shrink Small-Outline (DL) Packages**

NOTE: For tape and reel order entry:  
The DGG package is abbreviated to GR, and  
the DGV package is abbreviated to VR.

## description

The SN74CBTLV16212 provides 24 bits of high-speed bus switching or exchanging. The low on-state resistance of the switch allows connections to be made with minimal propagation delay.

The device operates as a 24-bit bus switch or a 12-bit bus exchanger, which provides data exchanging between the four signal ports via the data-select (S0, S1, S2) terminals.

The SN74CBTLV16212 is specified by the break-before-make feature to have no through current when switching between B ports.

The SN74CBTLV16212 is characterized for operation from  $-40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$ .

DGG, DGV, OR DL PACKAGE  
(TOP VIEW)

S0	1	56	S1
1A1	2	55	S2
1A2	3	54	1B1
2A1	4	53	1B2
2A2	5	52	2B1
3A1	6	51	2B2
3A2	7	50	3B1
GND	8	49	GND
4A1	9	48	3B2
4A2	10	47	4B1
5A1	11	46	4B2
5A2	12	45	5B1
6A1	13	44	5B2
6A2	14	43	6B1
7A1	15	42	6B2
7A2	16	41	7B1
V <sub>CC</sub>	17	40	7B2
8A1	18	39	8B1
GND	19	38	GND
8A2	20	37	8B2
9A1	21	36	9B1
9A2	22	35	9B2
10A1	23	34	10B1
10A2	24	33	10B2
11A1	25	32	11B1
11A2	26	31	11B2
12A1	27	30	12B1
12A2	28	29	12B2

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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FUNCTION TABLE

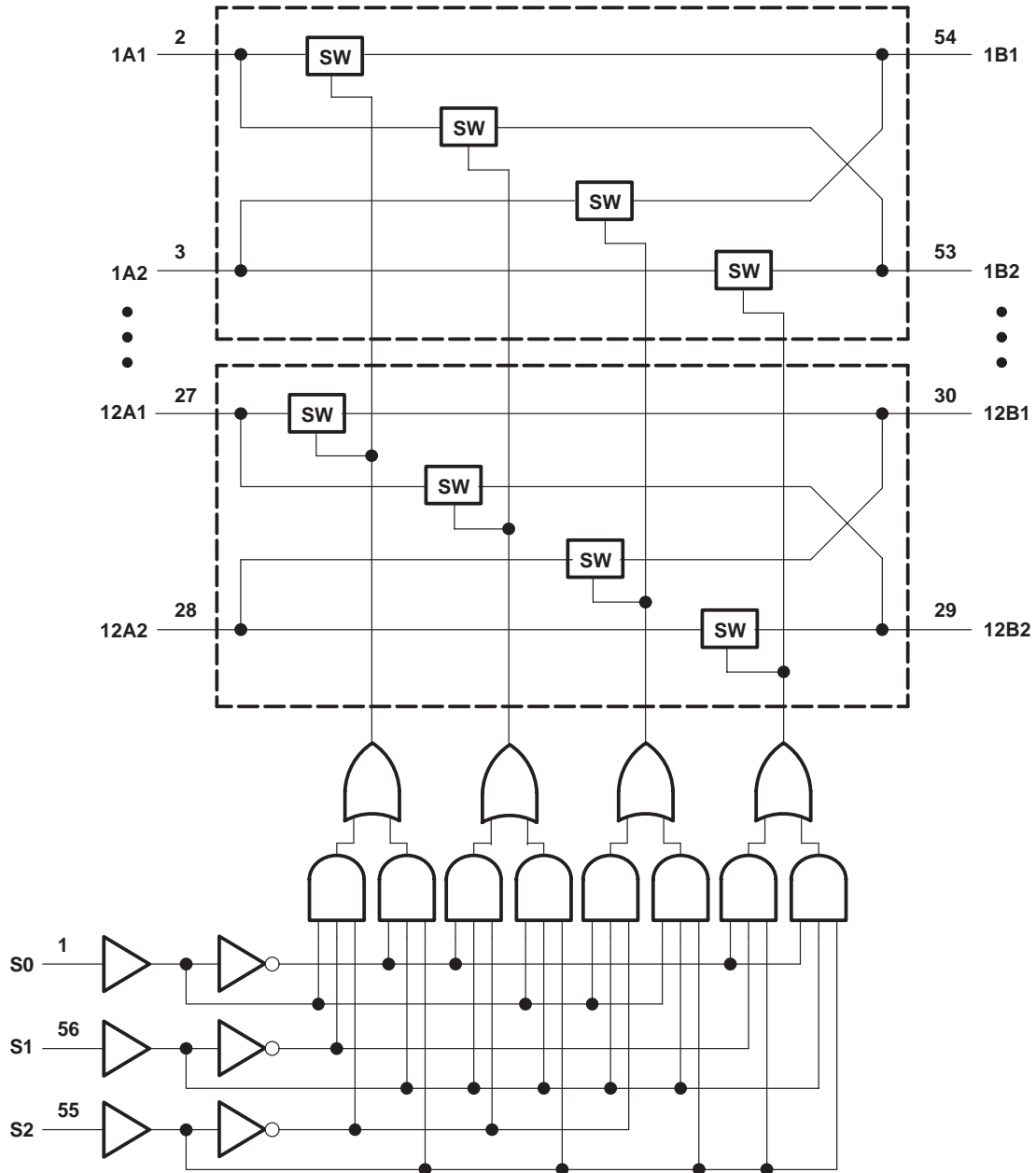
INPUTS			INPUTS/OUTPUTS		FUNCTION
S2	S1	S0	A1	A2	
L	L	L	Z	Z	Disconnect
L	L	H	B1	Z	A1 port = B1 port
L	H	L	B2	Z	A1 port = B2 port
L	H	H	Z	B1	A2 port = B1 port
H	L	L	Z	B2	A2 port = B2 port
H	L	H	Z	Z	Disconnect
H	H	L	B1	B2	A1 port = B1 port A2 port = B2 port
H	H	H	B2	B1	A1 port = B2 port A2 port = B1 port

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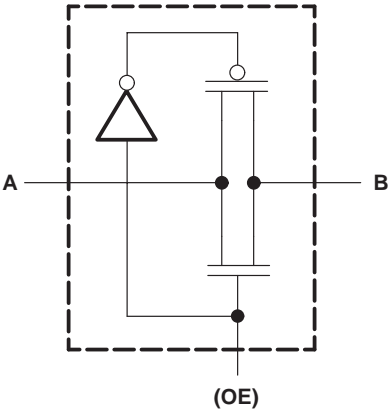
logic diagram (positive logic)



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simplified schematic, each FET switch



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, $V_{CC}$	–0.5 V to 4.6 V
Input voltage range, $V_I$ (see Note 1)	–0.5 V to 4.6 V
Continuous channel current	128 mA
Input clamp current, $I_{IK}$ ( $V_I < 0$ )	–50 mA
Package thermal impedance, $\theta_{JA}$ (see Note 2): DGG package)	81°C/W
DGV package)	86°C/W
DL package)	74°C/W
Storage temperature range, $T_{stg}$	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.  
2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		2.3	3.6	V
V <sub>IH</sub>	High-level control input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2		
V <sub>IL</sub>	Low-level control input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V		0.8	
T <sub>A</sub>	Operating free-air temperature		−40	85	°C

NOTE 3: All unused control inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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## LOW-VOLTAGE 24-BIT FET BUS-EXCHANGE SWITCH

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**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT	
V <sub>IK</sub>		V <sub>CC</sub> = 3 V,	I <sub>I</sub> = −18 mA				−1.2	V	
I <sub>I</sub>		V <sub>CC</sub> = 3.6 V,	V <sub>I</sub> = V <sub>CC</sub> or GND				±1	μA	
I <sub>off</sub>		V <sub>CC</sub> = 0,	V <sub>I</sub> or V <sub>O</sub> = 0 to 3.6 V				10	μA	
I <sub>CC</sub>		V <sub>CC</sub> = 3.6 V,	I <sub>O</sub> = 0,	V <sub>I</sub> = V <sub>CC</sub> or GND			10	μA	
ΔI <sub>CC</sub> ‡	Control inputs	V <sub>CC</sub> = 3.6 V,	One input at 3 V,	Other inputs at V <sub>CC</sub> or GND			300	μA	
C <sub>i</sub>	Control inputs	V <sub>I</sub> = 3 V or 0					5	pF	
C <sub>io</sub> (OFF)		V <sub>O</sub> = 3 V or 0,	$\overline{OE}$ = V <sub>CC</sub>				8	pF	
r <sub>on</sub> §		V <sub>CC</sub> = 2.3 V, TYP at V <sub>CC</sub> = 2.5 V	V <sub>I</sub> = 0	I <sub>I</sub> = 64 mA			5	8	Ω
				I <sub>I</sub> = 24 mA			5	8	
			V <sub>I</sub> = 1.7 V,		I <sub>I</sub> = 15 mA			27	
		V <sub>CC</sub> = 3 V	V <sub>I</sub> = 0	I <sub>I</sub> = 64 mA			5	7	
				I <sub>I</sub> = 24 mA			5	7	
			V <sub>I</sub> = 2.4 V,		I <sub>I</sub> = 15 mA			10	

<sup>†</sup> All typical values are at  $V_{CC} = 3.3\text{ V}$  (unless otherwise noted),  $T_A = 25^\circ\text{C}$ .

<sup>‡</sup> This is the increase in supply current for each input that is at the specified voltage level rather than  $V_{CC}$  or GND.

<sup>§</sup> Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

**switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)**

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$		$V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$		UNIT
			MIN	MAX	MIN	MAX	
$t_{pd}$ <sup>¶</sup>	A or B	B or A		0.15		0.25	ns
$t_{pd}$	S	B or A	3	11.1	3	8.8	ns
$t_{en}$	S	A or B	3	10.9	3	8.6	ns
$t_{dis}$	S	A or B	1	8.7	2	8.8	ns

<sup>¶</sup> The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

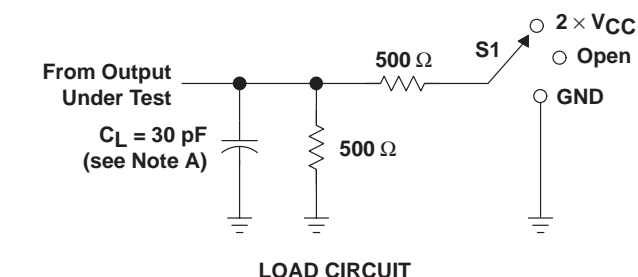
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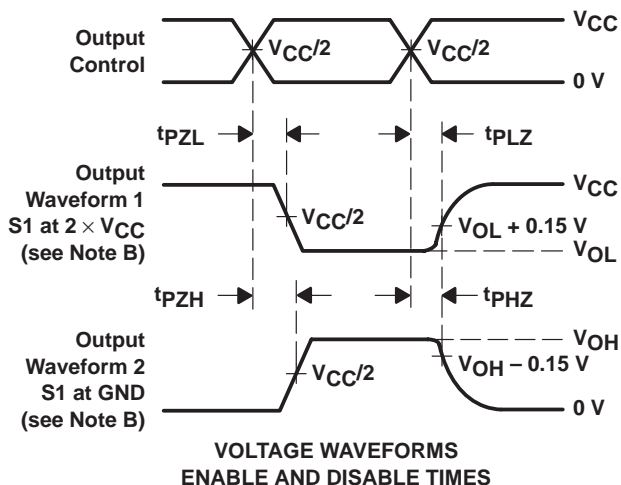
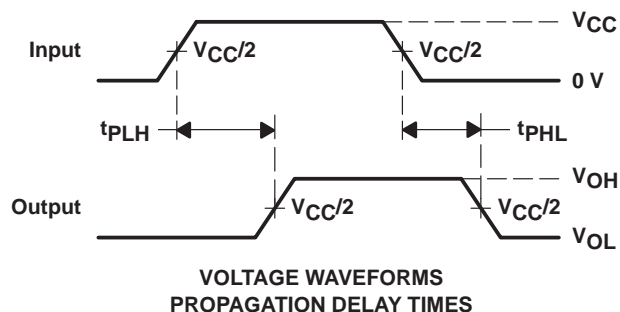
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### PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$$



TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	2 $\times V_{CC}$
$t_{PHZ}/t_{PZH}$	GND



- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_r \leq 2 \text{ ns}$ ,  $t_f \leq 2 \text{ ns}$ .
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

Figure 1. Load Circuit and Voltage Waveforms

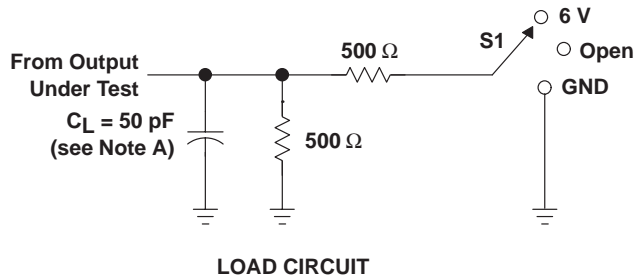
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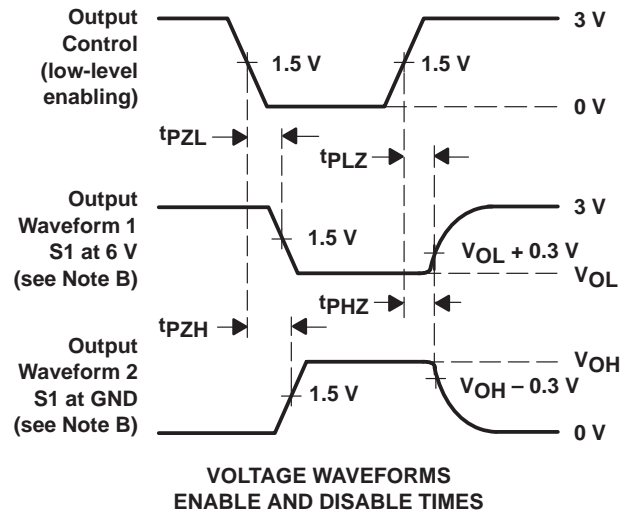
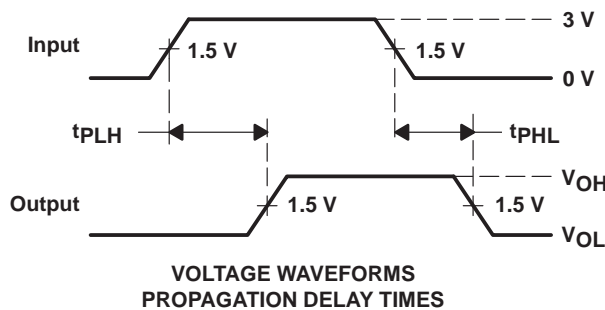
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### PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$$



TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	6 V
$t_{PHZ}/t_{PZH}$	GND



- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_r \leq 2.5 \text{ ns}$ ,  $t_f \leq 2.5 \text{ ns}$ .
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

Figure 2. Load Circuit and Voltage Waveforms

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